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Docket No.: 005199 USA/Consilium/Consilium

PATENT/OFFICIAL



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of :  
Yuehshian T. CHI et al. :  
Serial No. 09/725,908 : Group Art Unit: 2152  
Filed: November 30, 2000 : Examiner:

For: DYNAMIC SUBJECT INFORMATION GENERATION IN MESSAGE SERVICES OF  
DISTRIBUTED OBJECT SYSTEMS

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Honorable Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

This submission does not constitute a representation that a search has been made or that no better art exists and does not constitute an admission or representation that any of the listed documents is material or constitutes prior art. If it should be determined that any of the listed documents does not constitute prior art under the United States law, Applicants reserve the right

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to present to the Office the relevant facts and law regarding the appropriate status of such document.

No certification or fee is believed to be required. However, the Commissioner is hereby authorized to charge any additional fees should any be required for this submission, or credit any overpayment to deposit account no. 08-0219.

Respectfully submitted,

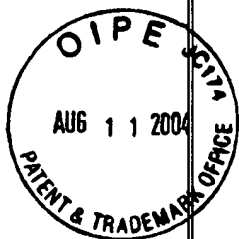
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**INFORMATION DISCLOSURE  
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APPLICATION  
(PTO-1449)**

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SERIAL NO.  
09/725,908

APPLICANT  
Yuehshian T. CHI et al.

FILING DATE  
November 30, 2000

GROUP  
2152


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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)</b>				ATTY. DOCKET NO. 005199 USA/ Consilium/Consilium		SERIAL NO. 09/725,908	
				APPLICANT Yuehshian T. CHI et al.			
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